

Docket No.: 50090-318

#8/Amend B  
Patent  
7/31/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



Re Application of

Shifumi TAKATA, et al.

Serial No.: 09/903,760

Filed: July 13, 2001

Group Art Unit: 2822

Examiner: J. Mitchell

For: SEMICONDUCTOR DEVICE HAVING AN IMPROVED INTERLAYER  
CONDUCTOR CONNECTIONS AND A MANUFACTURING METHOD  
THEREOF

RECEIVED  
JUL 22 2002  
TECHNOLOGY CENTER 2800

AMENDMENT

Commissioner for Patents  
Washington, DC 20231

Sir:

The following Amendment and Remarks are submitted in response to the Office  
Action dated April 19, 2002.

**IN THE CLAIMS:**

Please amend claim 9 as follows.

9. (Amended) A method of manufacturing a semiconductor device  
comprising the steps of:  
forming a first interlayer insulating film on a semiconductor substrate;  
forming a plurality of openings in said first interlayer insulating film;  
forming a conductor film on said first interlayer insulating film so as to fill said  
openings;